# Program of RJUSE TeraTech-2021

### MONDAY, Nov. 1st, 2021

10:15-10:25	Opening	
Session Mo1 10:25-11:15	Plasmonic THz	: <b>Devices I</b> Chair: Taiichi Otsuji ( <i>Tohoku University, Japan</i> )
	10:25-11:15 Mo1-1	Terahertz plasmonics: from terahertz detection and spectroscopy to twisted plasmons Michael S. Shur
	Plenary	Rensselaer Polytechnic Institute, USA
11:15-11:30	Coffee Break	
Session Mo2	Granhono THz	Devices I
11:30-13:00		Chair: Vladimir Mitin ( <i>University at Buffalo, USA</i> )
	11:30-12:00 Mo2-1	Plasma instability and generation of THz radiation using graphene-based field-effect transistors and lateral diodes with the coulomb electron drag
	Invited	Victor Ryzhii Institute of Ultra-High Frequency Semiconductor Electronics, Russia
	12:00-12:30 Mo2-2 Invited	Plasmon scattering in graphene junctions from scanning near-field microscopy simulations V. Perebeinos University at Buffalo, USA
	12:30-12:45 Mo2-3 Contributed	THz generation from Van der Waals crystals Chao Tang
	12:45-13:00 Mo2-4 Contributed	High speed terahertz detection by an asymmetric dual- grating-gate graphene FET Koichi Tamura Tohoku University, Japan

#### 13:00-14:15 Lunch

Session Mo3	Graphene THz Devices II	
14:15-15:45		Chair: Dmitry Svintsov ( <i>MIPT, Russia</i> )
	14:15-14:45 Mo3-1	Terahertz ratchet effects in graphene
	Invited	Sergey Ganichev
		Regensburg University, Germany
	14:45-15:15	Encapsulated graphene devices for the terahertz
	Mo3-2	technology
	Invited	Yahya M. Meziani
		Universidad de Salamanca, Spain
	15:15-15:30	Graphene plasmon transformation at a periodic
	Mo3-3	modulation of carrier density
	Contributed	Anastasiia Shirokova University of Nizhny Novgorod, Russia

15:30-15:45 Mo3-4	Strong polarization sensitivity in metal-graphene-metal far-infrared detectors
Contributed	Valentin Semkin Moscow Institute of Physics and Technology, Russia

#### 15:45-16:00 Coffee Break

Session Mo4 16:00-17:30	Narrow Bandgap Materials for THz Devices I		
	16:00-16:30 Mo4-1	THz and multi- THz stimulated emission of Dirac fermions in CdHgTe QW dielectric and "phonon" wavegueide	
	Invited	heterostructures: the present and future Sergey V. Morozov	
		Inst. for Physics of Microstructures, Russia	
	16:30-17:00	Terahertz plasmon in narrow gap HgTe/CdHgTe quantum	
	Mo4-2	wells	
	Invited	Alexander A. Dubinov	
		Inst. for Physics of Microstructures, Russia	
	17:00-17:30	MBE growth of complex CdHgTe infrared detector, laser	
	Mo4-3	and nBn heterostructures	
	Invited	Nikolai Mikhailov	
		Novosibirsk State University, Russia	

#### 17:30-17:45 Coffee Break

Session Mo5	2D Electron Sy	vstems for THz Devices
17:45-19:00		Chair: Denis Fateev ( <i>IREE, Russia</i> )
	17:45-18:00	Thresholdless excitation of edge plasmons by transverse
	Mo5-1	current
	Contributed	Aleksandr S. Petrov
		Moscow Institute of Physics and Technology, Russia
	18:00-18:15	Dipole excitation of terahertz plasmons in electrically
	Mo5-2	biased two-dimensional electron systems
	Contributed	Aleksandr S. Petrov
		Moscow Institute of Physics and Technology, Russia
	18:15-18:30	The in-plane photoelectric effect - Experiment
	Mo5-3	
	Contributed	Wladislaw Michailow
		University of Cambridge , England
	18:30-19:00	The in-plane photoelectric effect – Theory
	Mo5-4	
	Invited	Sergey Mikhailov
		University of Augsburg, Germany

### TUESDAY, Nov. 2nd, 2021

Session Tu1	Nanostructured THz Devices		
11:30-12:30		Chair: Berardi Sensale-Rodriguez (The University of Utah, USA)	
	11:30-12:00	Fast switching based on a one-dimensional electron gas	
	Tu1-1	in a Y-shaped device	
	Invited	Vladimir V. Mitin	
		University at Buffalo, USA	
	12:00-12:30 Tu1-2	Terahertz detection by thermomechanical transduction	
	Invited	Kazu Hirakawa	
		University of Tokyo, Japan	
12:30-14:15	Lunch		
Session Tu2	Nonlinear THz	Generation	
14:15-15:50		Chair: Kosuke Murate ( <i>Nagoya University</i> , <i>Japan</i> )	
	14:15-15:05	Leading-edge THz-wave research opened up by nonlinear	
	Tu2-1	photon-conversion devices	
	Plenary	Hiroaki Minamide	
		RIKEN Center for Advanced Photonics, Japan	
	15:05-15:20	Multiphoton ionization fronts in ZnS for terahertz light	
	Tu2-2	conversion	
	Contributed	M. A. Kurnikov	
		Novosibirsk State University, Russia	
	15:20-15:35	Generation of unipolar electromagnetic missiles by	
	Tu2-3	optical rectification of ultrashort laser pulses	
	Contributed	Alina Novokovskaya	
		University of Nizhing Novgorod, Russia	
	15:35-15:50 Tu2-4	Terahertz emission from epitaxial InAs	
	Contributed	Valerii Trukhin	
		loffe Institute, Russia	
15:50-16:05	Coffee Break		
Session Tu?	Granhene TH7	Devices III	
16:05-17:50	Graphene 112	Chair: Yahva M. Meziani (Universidad de Salamanca, Spain)	
	16:05-16:35	Graphene Diodes for Terahertz Rectification	
	Invited	Max Lemme	
		Aachen University. Germany	
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16:35-17:05	Tunnel field-effect transistors for terahertz detection
Tu3-2	
Invited	Dmitry Svintsov

		Moscow Institute of Physics and Technology, Russia
	17:05-17:35 Tu3-3 Invited	Photovoltaics of spatially modulated bilayer graphene: evidence of hydrodynamic regime Valentin Kachorovskii loffe Physico-Technical Institute, Russia
	17:35-17:50 Tu3-4 Contributed	Unveiling the microscopic origin of the terahertz conductance in strained polycrystalline graphene Simone Zanotto NEST, Istituto Nanoscienze, Italy
17:50-18:05	Coffee Break	
Session Tu4	Narrow Bandg	ap Materials for THz Devices II
18:05-19:05		Chair: Sergey Mikhailov (University of Augsburg, Germany)
	18:05-18:35 Tu4-1 Invited	Terahertz and multiterahertz nonlinear responses in 3D Dirac semimetal Cd3As2 Ryusuke Matsunaga <i>University of Tokyo, Japan</i>
	18:35-19:05 Tu4-2 Invited	Lorentz-driven Landau emission of Dirac and Kane fermions in graphene and CdHgTe bulk films Frederic Teppe University of Montpellier and CNRS, France

## WEDNESDAY, Nov. 3rd, 2021

Session We1 10:15-11:45	Carrier Dynamics and Material Properties in THz Regime I Chair: Michael S. Shur ( <i>Rensselaer Polytechnic Institute, USA</i> )		
	10:15-11:45 We1-1 Invited	Magnonic simulations of terahertz ultrastrong light- matter coupling Junichiro Kono Rice University, USA	
	10:45-11:15 We1-2 Invited	THz characterization and applications of wide bandgap materials: III-Nitrides and gallium oxide Berardi Sensale-Rodriguez The University of Utah, USA	
	11:15-11:30 We1-3 Contributed	Hot carrier dynamics and electron-phonon coupling studied by time-resolved THz spectroscopy Masatsugu Yamashita RIKEN Center for Advanced Photonics, Japan	
	11:30-11:45	THz spectra of thermal degraded polyethylene	
	Contributed	Fumiki Iwasaki Shibaura Institute of Technology, Japan	
11:45-12:00	Coffee Break		
Session We2	Superconducting THz Devices		
12:00-12:50		Chair: Victor Ryzhii ( <i>IUHFSE, Russia</i> )	
	12:00-12:50 We2-1 Plenary	Superconducting single-photon detector technology on the way to the terahertz range Gregory N. Goltsman Moscow State Pedagogical University, Russia	
12:50-14:15	Lunch		
Session We3	THz Wireless C	Communications	
	14:15-15:05 We3-1 Plenary	<b>Terahertz photonics for sensing and communications</b> <b>applications</b> Tadao Nagatsuma <i>Osaka University, Japan</i>	
	15:05-15:35 We3-2 Invited	Technical issues in sub-terahertz band communications and 300 GHz CMOS transceivers Minoru Fujishima <i>Hiroshima University, Japan</i>	
	15:35-16:05 We3-3 Invited	<b>300 GHz links enabled by Yagi-Uda antenna</b> Guillaume Ducournau <i>Lille 1 University, France</i>	

#### 16:05-16:20 Coffee Break

Session We4	Plasmonic THz Devices II		
16:20-17:35		Chair: Frederic Teppe (U. Montpellier and CNRS, France)	
	16:20-16:50	Use of weak plasmon modes for detection and	
	We4-1 Invited	amplification of terahertz radiation Denis Fateev	
		Kotelnikov Institute of Radio Engineering and Electronics, Russia	
	16:50-17:05 We4-2	Giant enhancement of photovoltage from InP-based dual- grating-gate HEMT plasmonic THz detector due to 3D rectification effect	
	Contributed	Takumi Negoro <i>Tohoku University, Japan</i>	
	17:05-17:20 We4-3 Contributed	Modal analysis of 2D plasmon-polariton in plasmonic THz detector with 2D diffraction grating structure Yuma Sasaki Tohoku University, Japan	
	17:20-17:35 We4-4 Contributed	Optimal asymmetry of transistor-based terahertz detectors Alexander Shabanov <i>Moscow Institute of Physics and Technology, Russia</i>	

17:35-17:50 Coffee Break

Session We5	THz Measurement Methods I	
17:50-19:05	17:50-18:20 We5-1 Invited	Nanothermometry of hot electrons Susumu Komiyama
	18:20-18:50	University of Tokyo, Japan
	We5-2 Invited	GaN medium by LTEM Masayoshi Tonouchi Osaka University, Japan
	18:50-19:05 We5-3 Contributed	Depth super-resolution terahertz tomography for inspection inside of walls Homare Momiyama <i>Topcon corporation, Japan</i>

# THURSDAY, Nov. 4th, 2021

Session Th1 10:15-12:15	Electronic/Pho	otonic THz Devices and Components I Chair: Minoru Fujishima ( <i>Hiroshima University, Japan</i> )
	10:15-10:45 Th1-1 Invited	Recent progress of terahertz emitters using resonant tunneling diodes Masahiro Asada Tokyo Institute of Technology, Japan
	10:45-11:15 Th1-2 Invited	Photonics-assisted terahertz beam control Kazutoshi Kato Kyushu University, Japan
	11:15-11:45 Th1-3 Invited	Enhanced terahertz emission and detection through plasmonic nanocavities Mona Jarrahi <i>University of California at Los Angels, USA</i>
	11:45-12:00 Th1-4 Contributed	<b>Resonant-tunneling-diode oscillator array with zigzag arrangement for terahertz power combination</b> Mai Van Ta <i>Tokyo Institute of Technology, Japan</i>
	12:00-12:15 Th1-5 Contributed	Scaling rule of double-mixing conversion gain of UTC-PD- integrated HEMT on UTC-PD mesa size Dai Nakajima <i>Tohoku University, Japan</i>
12:15-14:15	Lunch	
Session Th2 14:15-16:15	Electronic/Pho	otonic THz Devices and Components II Chair: Hiroaki Minamide ( <i>RAP, Japan</i> )
	14:15-14:45 Th2-1 Invited	<b>Terahertz detection through strain-induced</b> <b>photoconductive devices</b> Dmitry Ponomarev <i>Institute of Ultra-High Frequency Semiconductor Electronics,</i> <i>Russia</i>
	14:45-15:15 Th2-2 Invited	Three-dimensional printing of photonic components for the terahertz band Enrique Castro Camus Philipps University of Marburg, Germany
	15:15-15:45 Th2-3 Invited	Nanomaterials and microstructures for THz devices Alessandro Tredicucci

University of Pisa, Italy

	15:45-16:15 Th2-4 invited	Germanium as an ultrabroadband THz material Manfred Helm Helmholtz-Zentrum Dresden-Rossendorf, Germany
16:15-16:30	Coffee Break	
Session Th3 16:30-17:20	Carrier Dynamics and Material Properties in THz Regime II Chair: Manfred Helm ( <i>HZDR. Germany</i> )	
	16:30-17:20 Th3-1 Plenary	<b>Terahertz enhacement of dynamic nuclear polarization in</b> <b>semiconductors</b> Wojciech Knap <i>CENTERA LABORATORIES , Institute of High Pressure Physics</i> <i>PAS, Poland</i>
17:20-17:35	Coffee Break	
Session Th4 17:35-18:50	THz Measurement Methods II Chair: Masayoshi Tonouchi (Osaka University, Japan)	
	17:35-18:05 Th4-1 Invited	Development of 300 GHz walk-through body scanner by THz radar technology Chiko Otani <i>RIKEN Center for Advanced Photonics, Japan</i>
	18:05-18:35 Th4-2 Invited	Development of terahertz parametric generator for real- time measurement Kosuke Murate Nagoya University, Japan
	18:35-18:50	THz Detection of E-waste
	Contributed	Toa Yoshizumi Shibaura Institute of Technology, Japan
18:50-19:00	Closing	